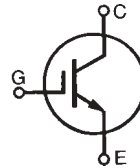


Trench IGBT

IXGA9289

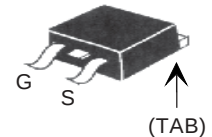
For Plasma Display Applications

(Development type IXGA_120N30TC)



$$\begin{aligned} V_{CES} &= 300 \text{ V} \\ I_{C25} &= 120 \text{ A} \\ V_{CE(sat)(typ)} &= 1.4 \text{ V} \end{aligned}$$

TO-263 (IXGA)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	300	V
V_{GEM}		± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$, IGBT chip capability	120	A
I_{C90}	$T_C = 90^\circ\text{C}$	75	A
I_{CM}	$T_J \leq 150^\circ\text{C}$, $t_p < 300 \mu\text{s}$	200	A
$I_{C(RMS)}$	Lead current limit	75	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 20 \Omega$ Clamped inductive load, $V_{CE} < 300 \text{ V}$	$I_{CM} = 100$	A
P_C	$T_C = 25^\circ\text{C}$	250	W
T_J		$-55 \dots +150$	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		$-55 \dots +150$	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Plastic body for 10s		260	$^\circ\text{C}$
M_d	Mounting torque (TO-3P)	1.3/10	Nm/lb.in.
Weight	TO-263	3	g

Features

- International standard packages
- Trench gate construction for low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity

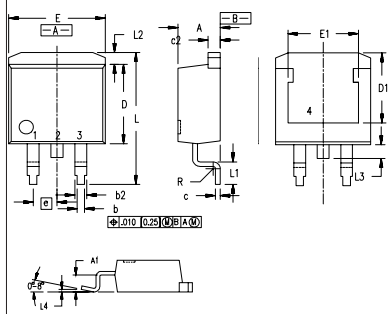
Applications

- PDP Screen Drivers
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$			1 μA
	$V_{GE} = 0 \text{ V}$			200 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 200 \text{ nA}$
$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}$, $I_C = 60 \text{ A}$	1.4	1.8	V
	$I_C = 120 \text{ A}$	1.7		V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{ A}$, $V_{CE} = 10\text{ V}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	60	85	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		5600	pF
C_{oes}			160	pF
C_{res}			38	pF
Q_g	$I_C = 60\text{ A}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		134	nC
Q_{ge}			34	nC
Q_{gc}			29	nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$ $I_C = 60\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 150\text{ V}$, $R_G = R_{off} = 5\text{ }\Omega$		33	ns
t_{ri}			43	ns
$t_{d(off)}$			73	ns
t_{fi}			24	ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$ $I_C = 60\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 150\text{ V}$, $R_G = R_{off} = 5\text{ }\Omega$		32	ns
t_{ri}			72	ns
$t_{d(off)}$			84	ns
t_{fi}			40	ns
R_{thJC}			0.5	K/W
R_{thCK}		0.25		K/W

TO-263 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	